

HIGH VOLTAGE POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

I _{F(AV)}	3 A
V _{RRM}	60 V
V _F (max)	0.59 V

PRELIMINARY DATASHEET

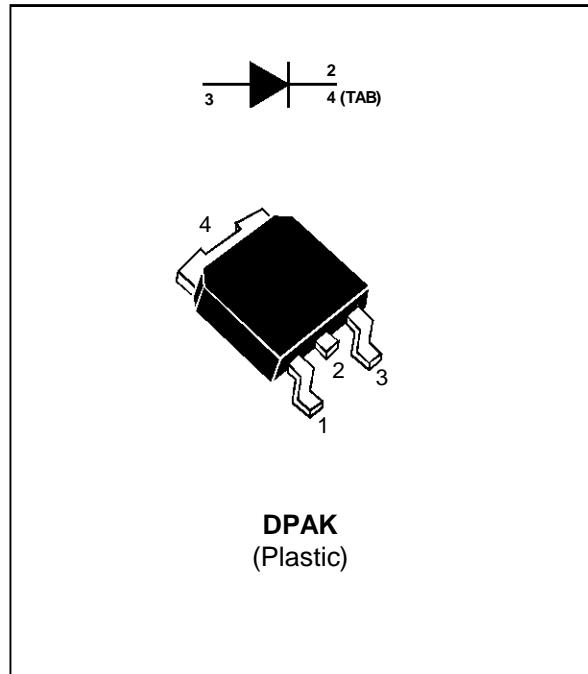
FEATURES AND BENEFITS

- NEGLIGIBLE SWITCHING LOSSES
- LOW FORWARD DROP VOLTAGE
- LOW CAPACITANCE
- HIGH REVERSE AVALANCHE SURGE CAPABILITY
- TAPE AND REEL OPTION : -TR

DESCRIPTION

High voltage Schottky rectifier suited to Switch Mode Power Supplies and other Power Converters.

Packaged in DPAK, this device is intended for use in medium voltage operation, and particularly, in high frequency circuitries where low switching losses are required.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{RRM}	Repetitive Peak Reverse Voltage	60	V
I _{F(RMS)}	RMS Forward Current	6	A
I _{F(AV)}	Average Forward Current	3	A
I _{FSM}	Surge Non Repetitive Forward Current	50	A
I _{RRM}	Repetitive Peak Reverse Current	1	A
T _{stg}	Storage Temperature Range	- 65 to + 150	°C
T _j	Max. Junction Temperature	150	°C
dV/dt	Critical Rate of Rise of Reverse Voltage	1000	V/μs

STPS360B(-TR)

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R_{TH} (j-c)	Junction to Case Thermal Resistance	3.5	°C/W

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Tests Conditions	Tests Conditions		Min.	Typ.	Max.	Unit
I_R *	Reverse leakage Current	$T_j = 25^\circ\text{C}$	$V_R = 60 \text{ V}$			30	μA
		$T_j = 125^\circ\text{C}$			2.5	10	mA
V_F **	Forward Voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 3 \text{ A}$			0.65	V
		$T_j = 125^\circ\text{C}$	$I_F = 3 \text{ A}$		0.55	0.59	

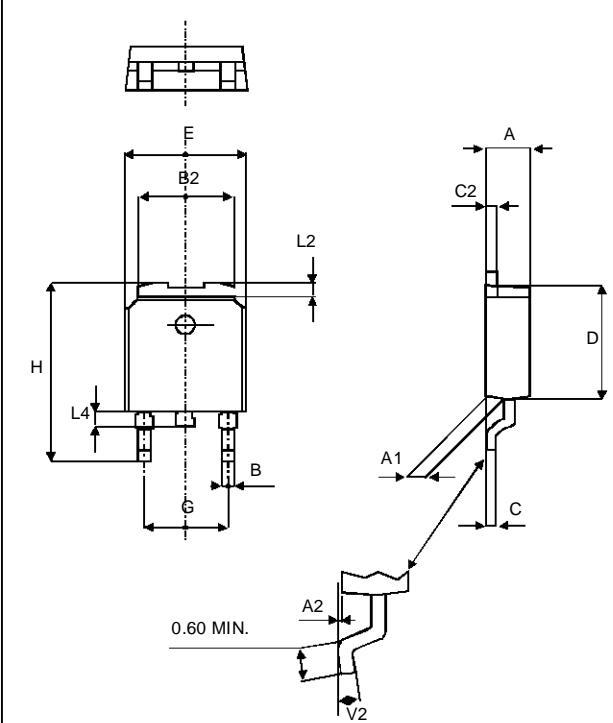
Pulse test : * $t_p = 380 \mu\text{s}$, duty cycle < 2 %

** $t_p = 5 \text{ ms}$, duty cycle < 2 %

To evaluate the maximum conduction losses use the following equation :

$$P = 0.49 \times I_{F(AV)} + 0.035 I_F^2(\text{RMS})$$

Typical junction capacitance, $V_R = 0\text{V}$ $F = 1\text{MHz}$ $T_j = 25^\circ\text{C}$ $C = 815\text{pF}$

PACKAGE MECHANICAL DATA
DPAK


REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.212
C	0.45		0.60	0.017		0.023
C2	0.48		0.60	0.018		0.023
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.251		0.259
G	4.40		4.60	0.173		0.181
H	9.35		10.10	0.368		0.397
L2		0.80			0.031	
L4	0.60		1.00	0.023		0.039
V2	0°		8°	0°		8°

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